

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A thermal treatment apparatus comprising:  
a furnace for heat-treating a substrate; and  
a substrate support for supporting the substrate in the furnace,  
wherein the substrate support has a main body portion and a supporting  
portion provided on the main body portion, the supporting portion being in contact with the  
substrate,  
the supporting portion is formed from a silicon plate-like member,  
a thickness of the supporting portion is not less than ~~twice a thickness of the~~  
substrate 3 mm and not more than 10 mm, and  
the supporting portion is not in contact with a periphery of the substrate.
- 2-4. (Canceled)
5. (Previously Presented) The thermal treatment apparatus according to claim 1,  
wherein a substrate-placing face of the supporting portion, on which the substrate is placed, is  
coated with an amorphous silicon oxide film.
6. (Currently Amended) A thermal treatment apparatus comprising:  
a furnace for heat-treating a substrate, and  
a substrate support for supporting the substrate in the furnace,  
wherein the substrate support has a main body portion and a supporting  
portion provided on the main body portion, the supporting portion being in contact with the  
substrate,  
the supporting portion is formed from a silicon plate-like member,

a thickness of the supporting portion is not less than ~~twice a thickness of the~~  
~~substrate~~ 3 mm and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and  
a substrate-placing face of the supporting portion, on which the substrate is  
placed, is coated with a film or films comprising one or more materials including silicon  
carbide, silicon nitride, polycrystalline silicon, silicon oxide, glassy carbon, and  
microcrystalline diamond.

7-11. (Canceled)

12. (Previously Presented) The thermal treatment apparatus according to claim 6,  
wherein an uppermost film of the film or the films is an amorphous silicon oxide film.

13-14. (Canceled)

15. (Withdrawn) A method for manufacturing a substrate, comprising:  
carrying a substrate into a furnace;  
supporting the substrate by a supporting portion formed from a silicon plate-  
like member having a thickness not less than twice a thickness of the substrate and not more  
than 10 mm, the supporting portion not being in contact with a periphery of the substrate;  
heat-treating the substrate in the furnace with the substrate being supported by  
the supporting portion; and  
carrying the substrate out of the furnace.

16. (Withdrawn) A method for manufacturing a substrate, comprising:  
carrying a substrate into a furnace;  
supporting the substrate by a supporting portion  
heat-treating the substrate in the furnace with the substrate being supported by  
the supporting portion; and  
carrying the substrate out of the furnace,

wherein the supporting portion is formed from a silicon plate-like member,  
a thickness of the supporting portion is not less than twice a thickness of the  
substrate and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and  
a substrate-placing face of the supporting portion, on which the substrate is  
placed, is coated with a film or films comprising one or more materials including silicon  
carbide, silicon nitride, polycrystalline silicon, silicon oxide, glassy carbon, and  
microcrystalline diamond.

17. (Withdrawn) A method for manufacturing a semiconductor device,  
comprising:

carrying a substrate into a furnace;

supporting the substrate by a supporting portion formed from a silicon plate-  
like member having a thickness not less than twice a thickness of the substrate and not more  
than 10 mm, the supporting portion not being in contact with a periphery of the substrate;

heat-treating the substrate in the furnace with the substrate being supported by  
the supporting portion; and

carrying the substrate out of the furnace.

18. (Withdrawn) A method for manufacturing a semiconductor device,  
comprising:

carrying a substrate into a furnace;

supporting the substrate by a supporting portion;

heat-treating the substrate in the treatment room with the substrate being  
supported by the supporting portion; and

carrying the substrate out of the furnace,

wherein the supporting portion is formed from a silicon plate-like member,

a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm,

the supporting portion is not in contact with a periphery of the substrate, and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with a film or films comprising one or more materials including silicon carbide, silicon nitride, polycrystalline silicon, silicon oxide, glassy carbon, and microcrystalline diamond.

19. (Currently Amended) A thermal treatment apparatus comprising:

a furnace for heat-treating a substrate; and

a substrate support for supporting the substrate in the furnace,

wherein the substrate support has a supporting portion which is in contact with the substrate and a main body portion which supports the supporting portion,

the main body portion is formed from a silicon carbide,

the supporting portion is formed from a silicon plate-like member and a

thickness of the supporting portion is not less than ~~twice a thickness of the substrate~~ 3 mm

and not more than 10 mm,

a diameter of the supporting portion is smaller than a diameter of the substrate,

and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with an amorphous silicon oxide film.

20. (Currently Amended) A thermal treatment apparatus comprising:

a furnace for heat-treating a substrate; and

a substrate support for supporting the substrate in the furnace,

wherein the substrate support has a supporting portion that is in contact with the substrate and a plate that supports the supporting portion and a main body portion which supports the plate,

the supporting portion is formed from a silicon plate-like member and a thickness of the supporting portion is not less than ~~twice a thickness of the substrate~~ 3 mm and not more than 10 mm,

a diameter of the supporting portion is smaller than a diameter of the substrate and a diameter of the plate, and

a substrate-placing face of the supporting portion, on which the substrate is placed, is coated with an amorphous silicon oxide film.

21. (Previously Presented) The thermal treatment apparatus according to claim 20, wherein the plate and the main body portion are formed from a silicon carbide.